

# Fiber-GRIN Alignment tool KLZ 16/0422

PROJECT NUMBER: 12422 (HYAZINT)

CLEANROOM START: 29.07.2016

CLEANROOM END: 31.08.2016

## Short description of the fabricated chips:

### SUBSTRATES:

- 1 x Si-SiO<sub>x</sub>(400 nm)-Nitride(108 nm), DSP, 100 mm, Batch 068 Ox3, 380 µm

### STRUCTURES:

- KOH etched grooves for alignment

### MASK SET:

- "0 KOH"

Process	Comments
1. <u>HMDS-priming:</u> <input type="checkbox"/>	
<ul style="list-style-type: none"> <li>• HDMS hotplate (Program 1)</li> </ul>	
2. <u>Spin Coating of positive resist:</u> <input type="checkbox"/>	
<ul style="list-style-type: none"> <li>• Nominal thickness: 1.8 µm</li> <li>• Statically dispense <b>2.0 mL</b> of <b>AZ1518</b> (Position 4 on 25 mL syringe)</li> <li>• <b>Recipe 4:</b> 4000 rpm, 30 sec</li> </ul>	<i>Profilometer: 2 µm PR thickness measured</i>
3. <u>Softbake:</u> <input type="checkbox"/>	
<ul style="list-style-type: none"> <li>• <b>100°C, 50 s</b></li> </ul>	
4. <u>Exposure: "0 KOH"</u> <input type="checkbox"/>	
<ul style="list-style-type: none"> <li>• Flat alignment, foil mask, soft contact</li> <li>• Exposure time: <b>5 s</b> = 2.8 s x 1.8 @ 9mW</li> </ul>	
5. <u>Develop</u> <input type="checkbox"/>	
<ul style="list-style-type: none"> <li>• <b>Program P</b></li> </ul>	
6. <u>Structure oxide: RIE (STS)</u> <input type="checkbox"/>	
<ul style="list-style-type: none"> <li>• Nitride thickness: 108 nm</li> <li>• Oxide thickness: 400 nm</li> </ul>	<i>He leakage rate &gt; 50 mT/min. Etched anyway. No problems visible.</i>
7. <u>Resist stripping</u> <input type="checkbox"/>	

Process	Comments
8. <u>KOH Etching</u> <input type="checkbox"/>	
<ul style="list-style-type: none"><li>Desired depth: 180 um</li><li>Concentration: 30 %\</li><li>T = 80 C</li><li>Depth tolerance: &gt; 180 um</li></ul>	Measured depth: 183 um